



Bremsstrahlung Measurements with SECRAL-II Ion Source

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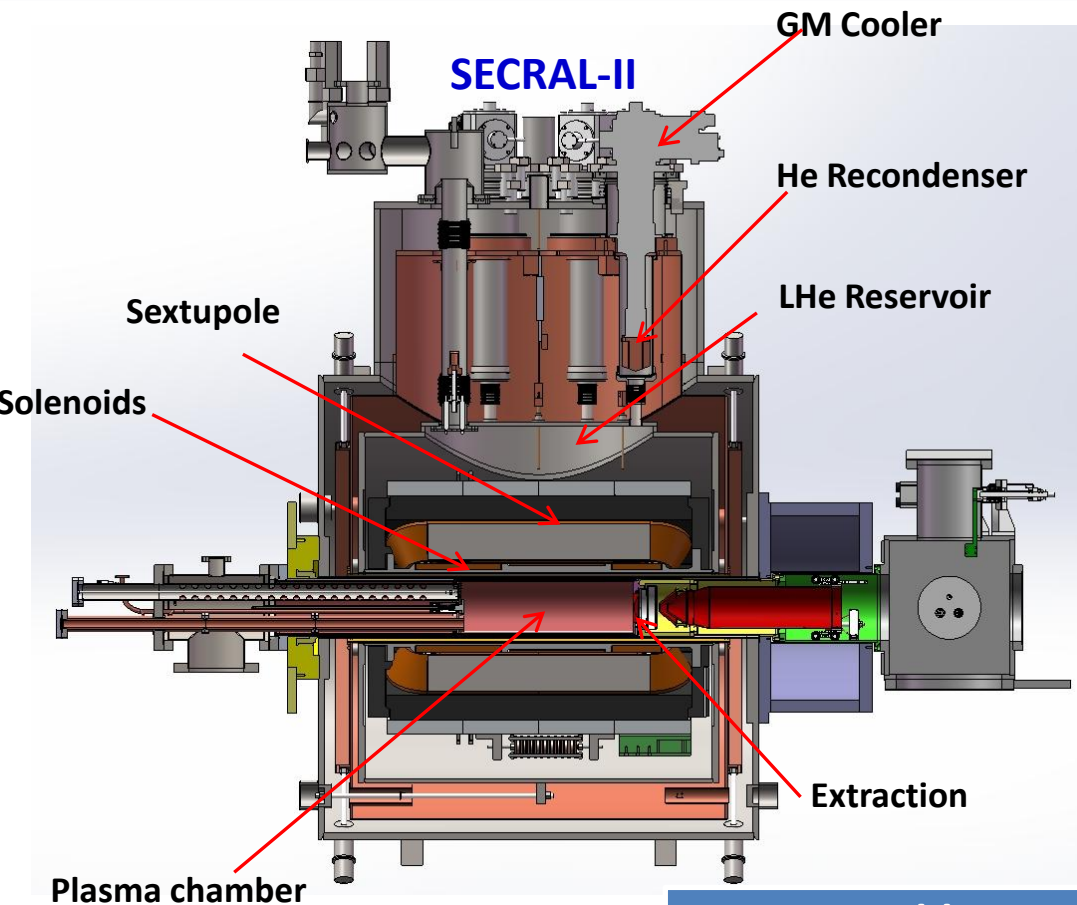
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- I. Quick Overview**
- II. X-ray Measurement Setup with SECRAL-II**
- III. Analysis of Bremsstrahlung Spectra**
- IV. Investigation and Results**
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Quick Overview



Key Parameters

ω_{rf} (GHz)	18-28
Axial Field Peaks (T)	3.7 (Inj.), 2.2 (Ext.)
Mirror Length (mm)	420
No. of Axial SNs	3
B_r at Chamber Inner Wall (T)	2.0
Magnet Cooling	LHe bathing
Chamber ID (mm)	125.0
Dynamic cooling power (W)	~6

Bremsstrahlung Spectra &
Spectral Temperature T_s

Aim of Research

Magnetic Field Configuration

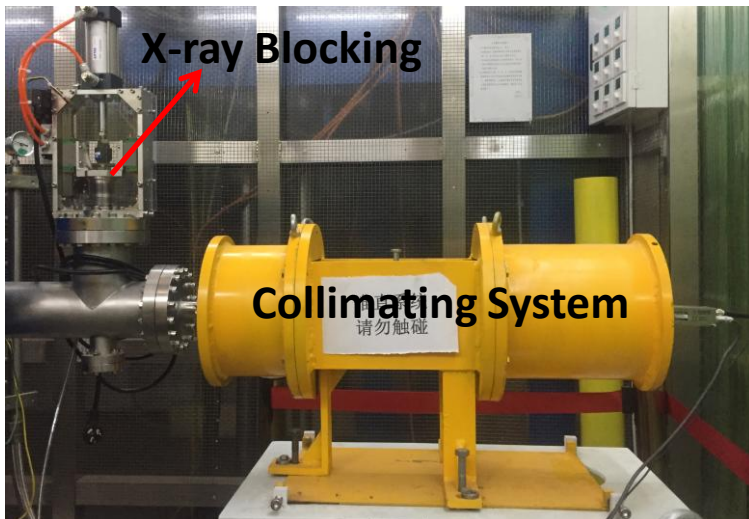
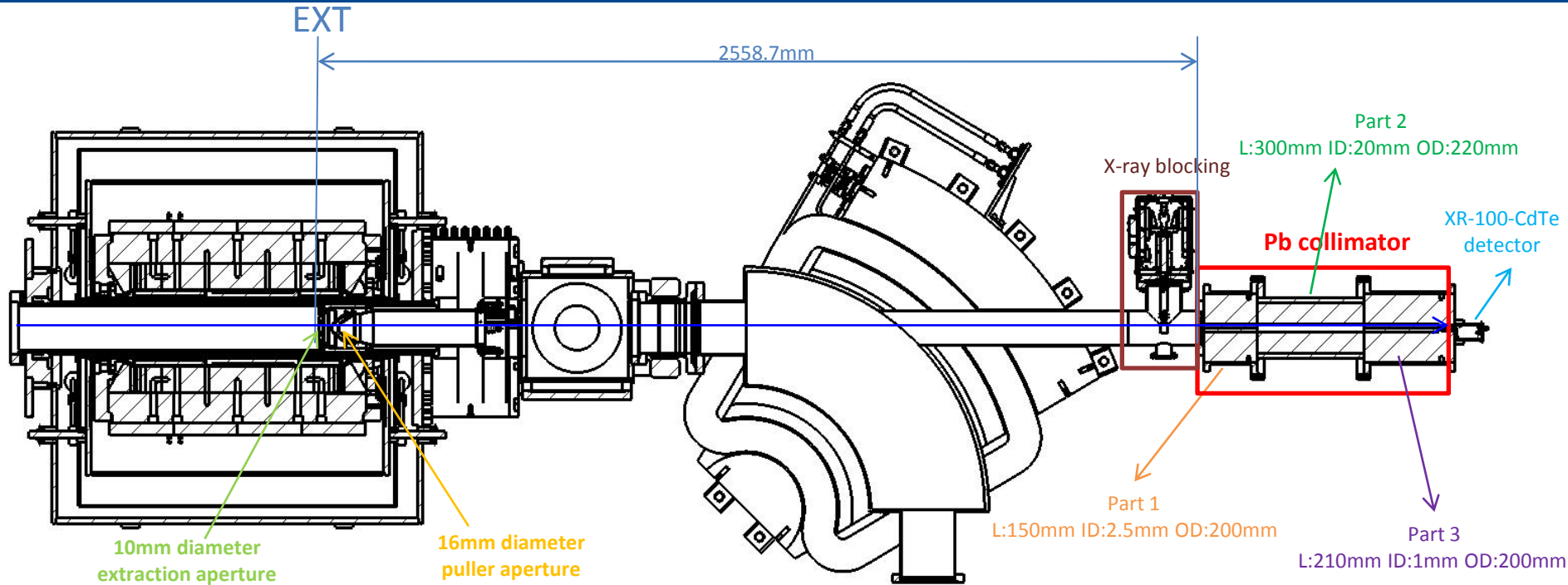
RF Power

Gas Pressure

Bias Voltage

HV

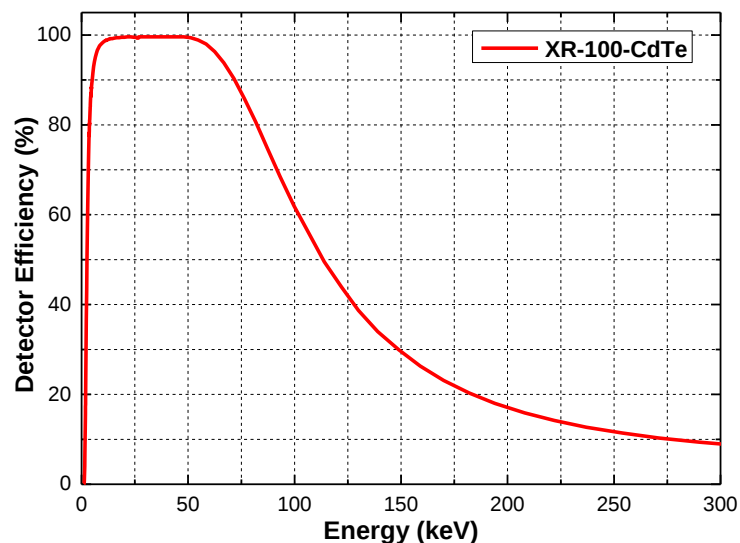
X-ray Measurement Setup with SECRAL-II



- Designed using **MCNP** code to avoid
 - I. Thick target bremsstrahlung
 - II. Secondary radiation

XR-100-CdTe Detector

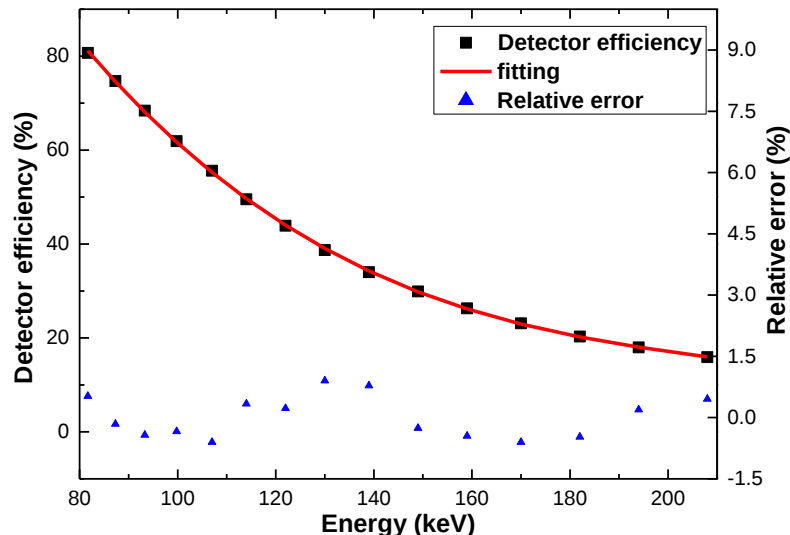
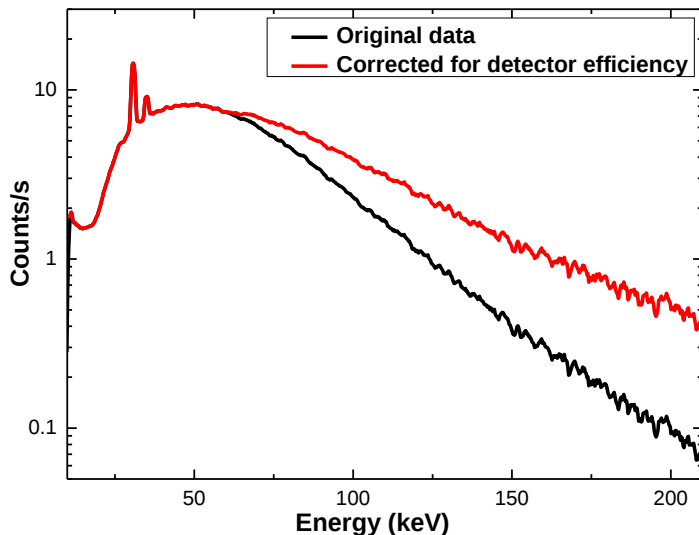
Detector type	Cadmium Telluride (CdTe) Diode
Detector areas	3 x 3 mm (9 mm ²)
Detector thickness	1 mm
Energy resolution @ 122 keV, ⁵⁷ Co	<1.5 keV FWHM, typical
Detector window	Be: 4 mil thick (100 μm)
Energy range	10 – 300 keV
Detector efficiency	See below



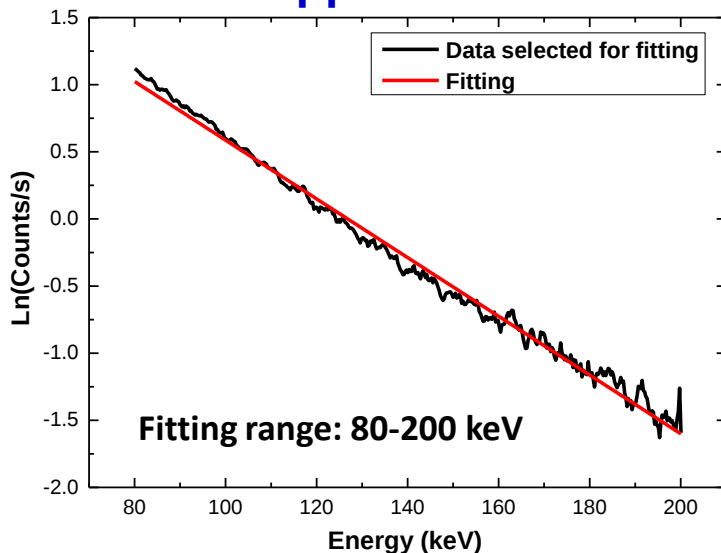
Analysis of Bremsstrahlung Spectra

I. Calibration applied

II. Spectra corrected for detector efficiency



III. Linear fit applied

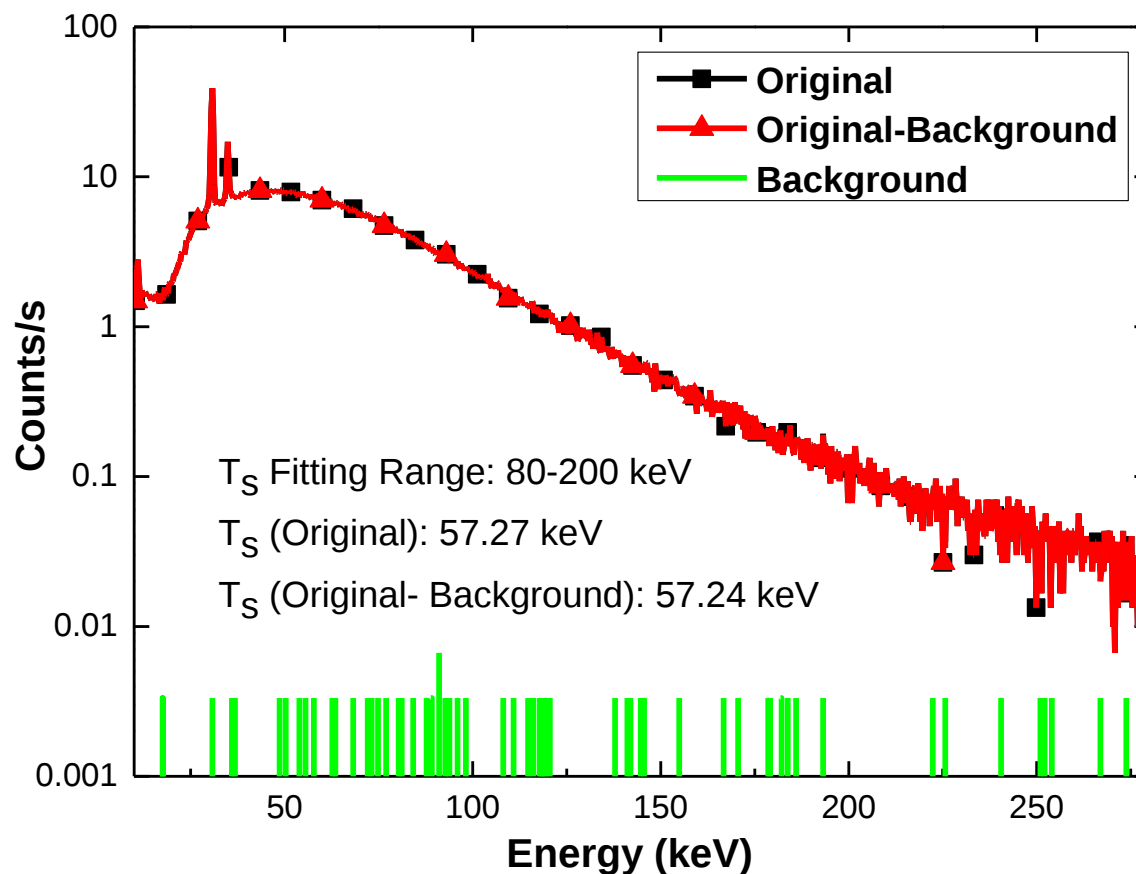


$$\text{Spectral Power } j(\hbar\omega) \propto \exp(-\hbar\omega/T_s)$$

In semi-log plot

$$T_s = -1/\text{slope}$$

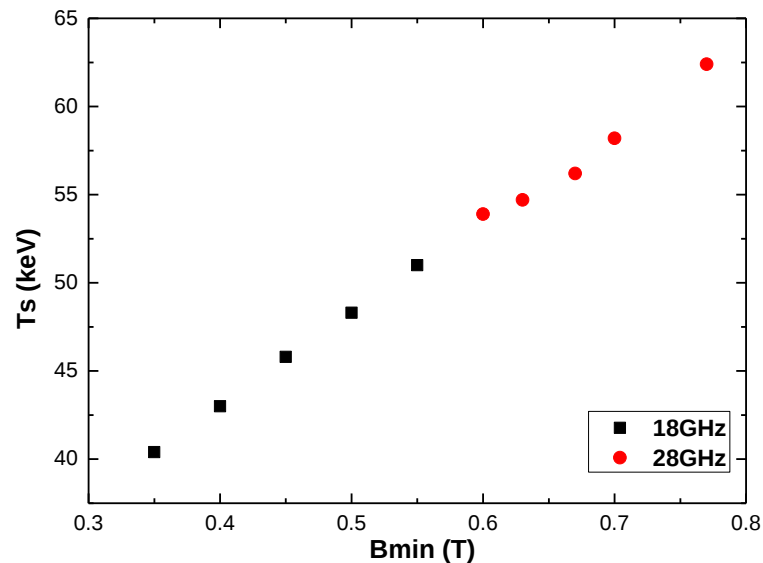
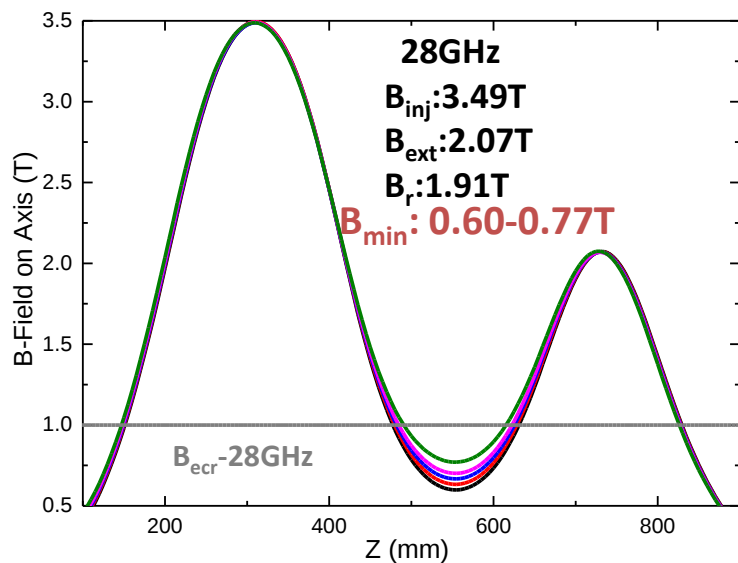
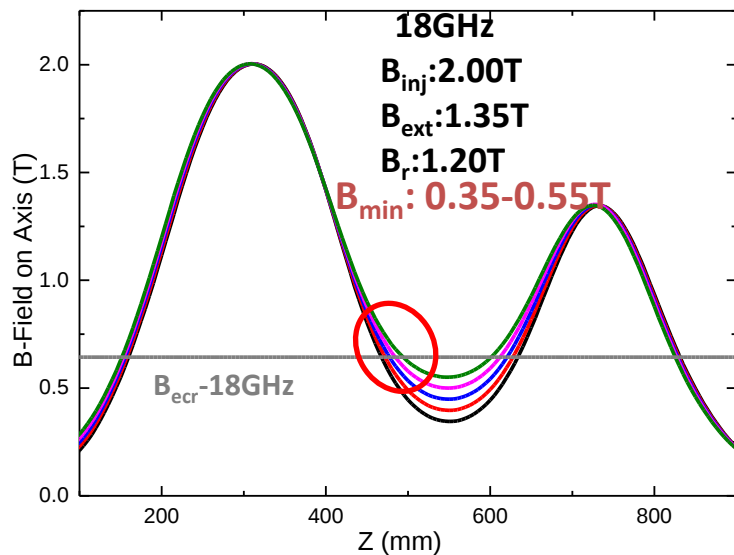
Efficiency of Collimating System



- Difference (with or without background) of T_S is **less than 0.06%**
- All data presented in the following sections are spectra without background subtraction

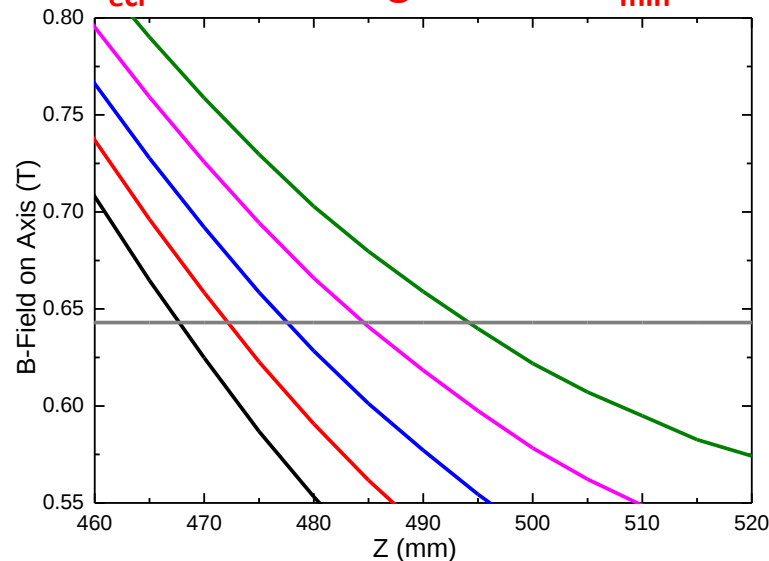


Constant B_{inj} , B_{ext} and B_r while Varying B_{min}

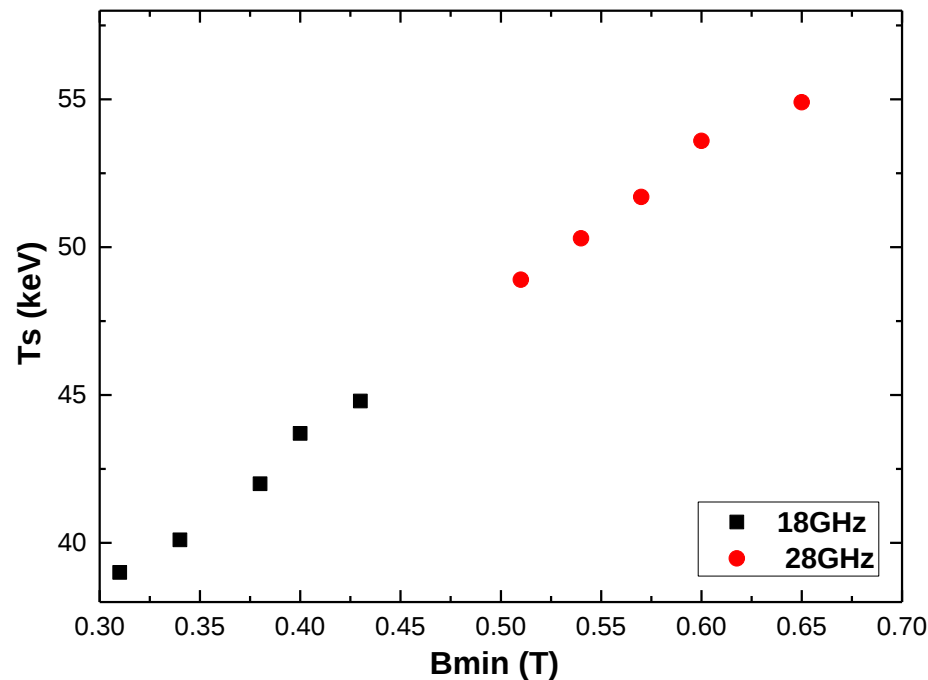
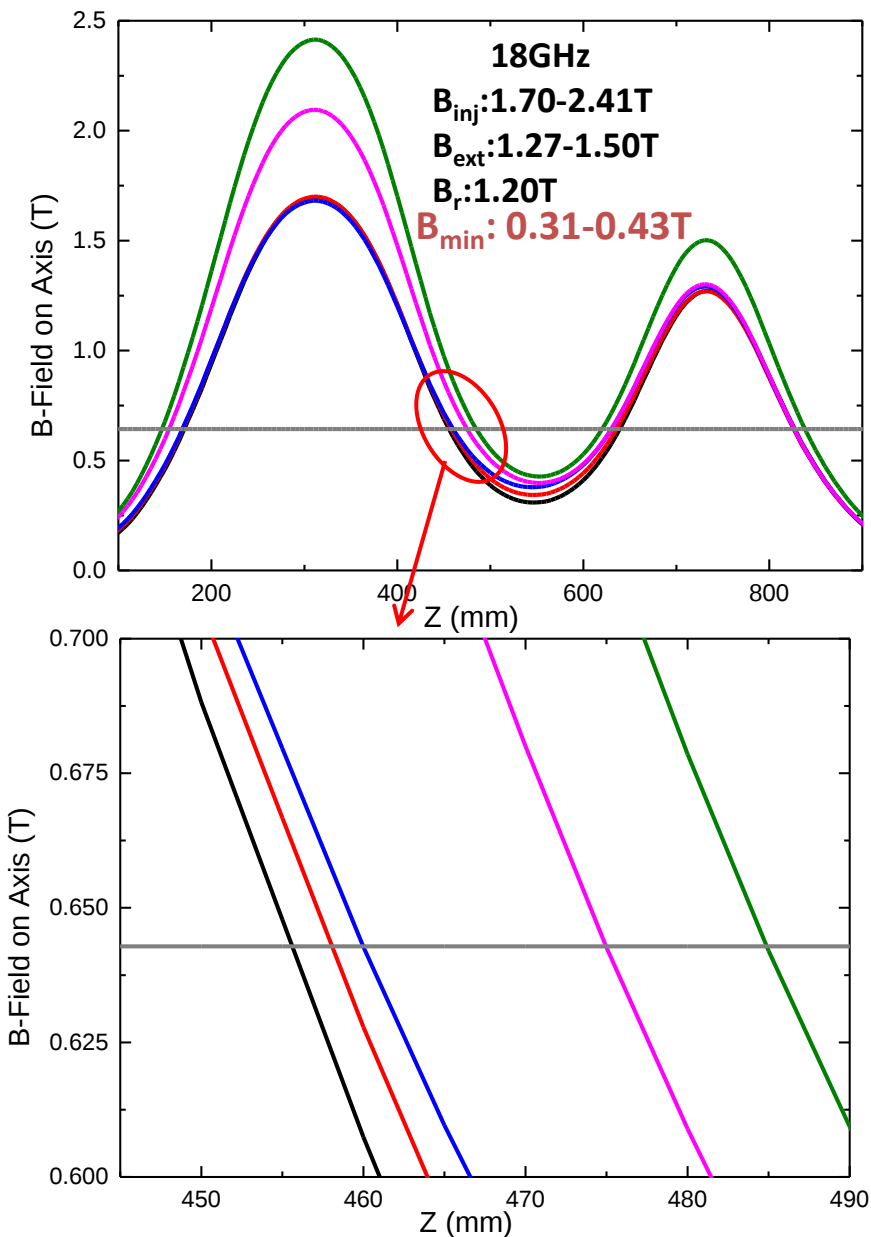


➤ T_s appears to be a function of B_{min}

Note: ∇B_{ecr} is also changed when B_{min} is changed

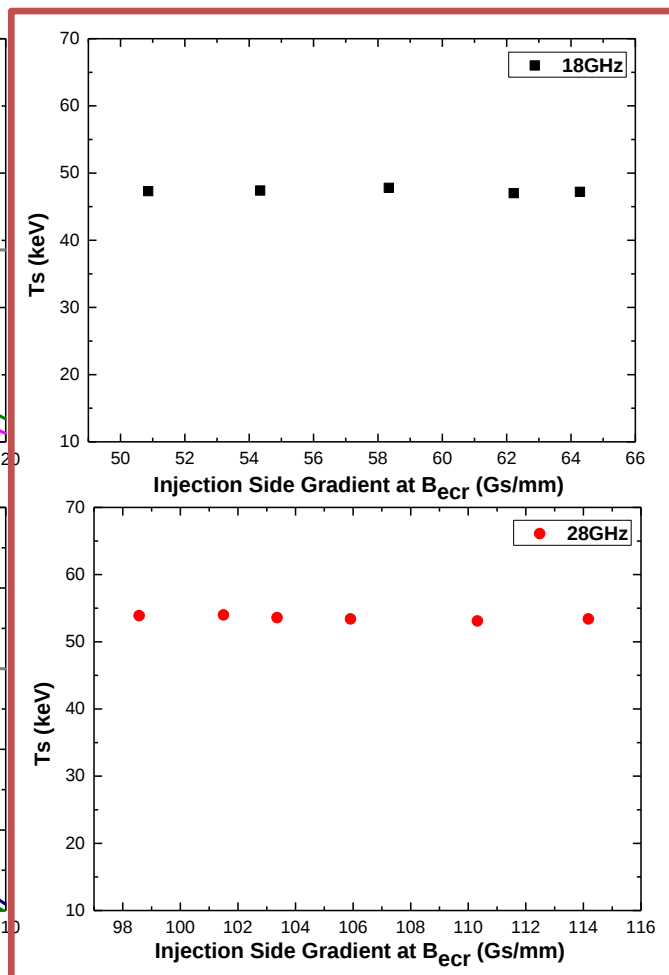
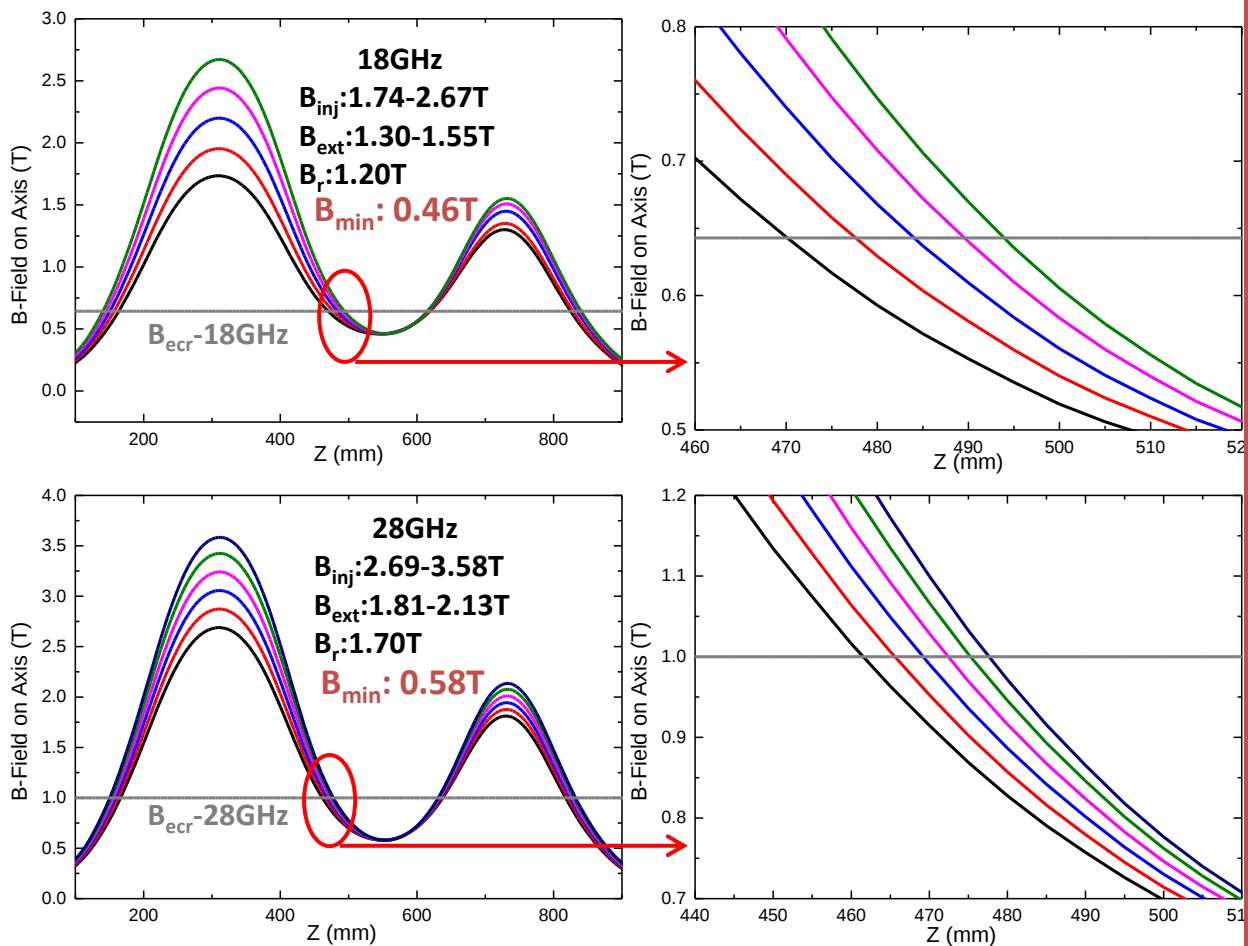


Constant ∇B_{ecr} while Varying B_{min}



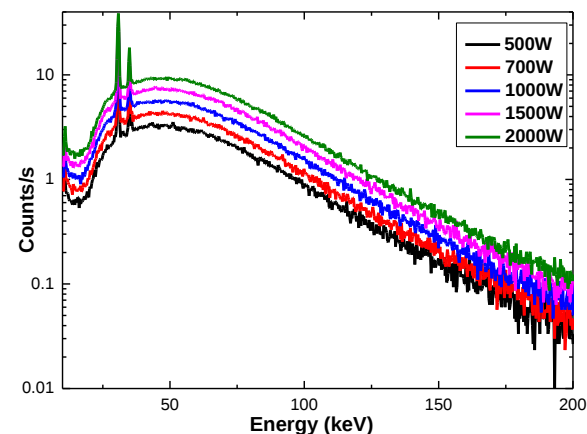
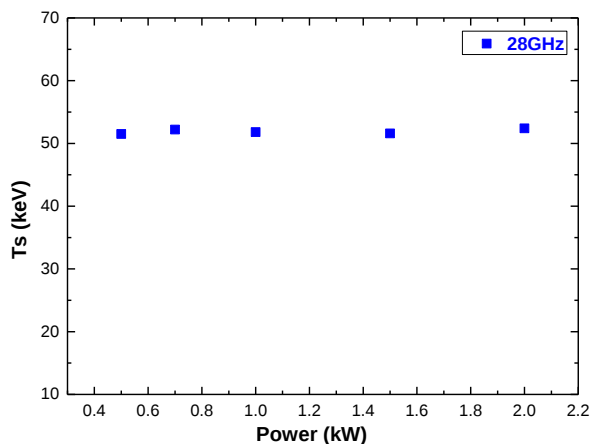
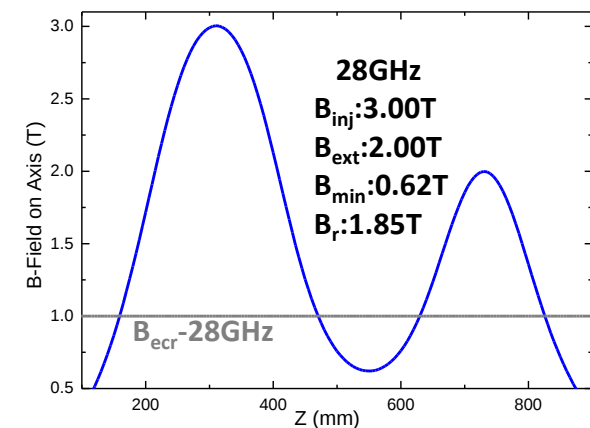
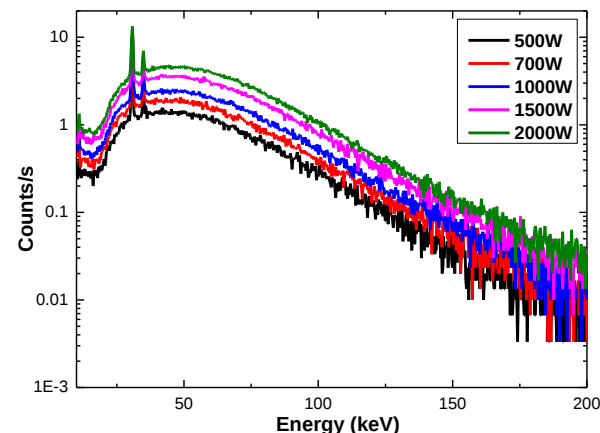
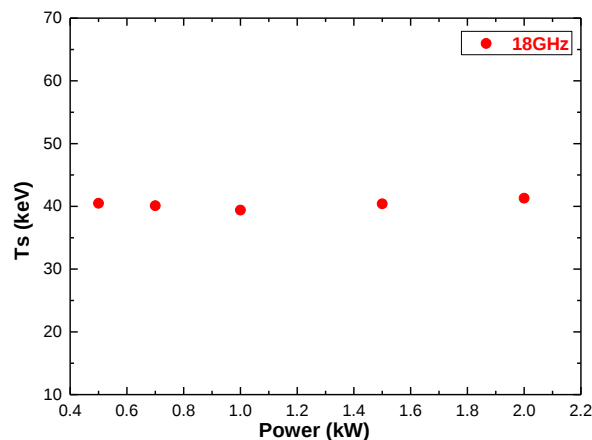
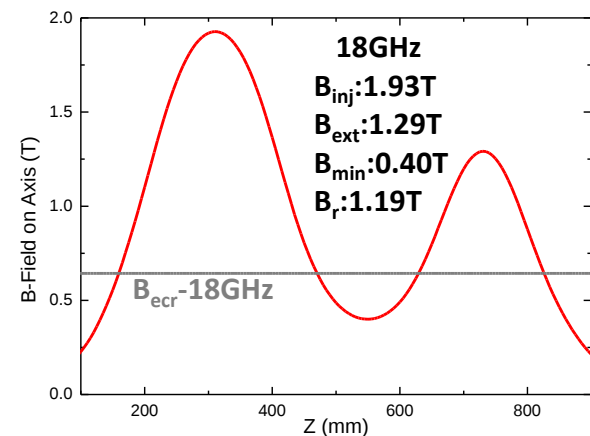
- For 18GHz, B_{min} was varied by **38%** while ∇B_{ecr} was varied by **9%**
- For 28GHz, B_{min} was varied by **27%** while ∇B_{ecr} was varied by **9%**
- It seems that T_s depends linearly on B_{min}

Constant $B_{\min}$ while Varying ∇B_{ecr}



- For 18GHz, ∇B_{ecr} was varied by **26%** while T_s was varied by **1%**
- For 28GHz, ∇B_{ecr} was varied by **16%** while T_s was varied by **1%**
- T_s does not depend on ∇B_{ecr}

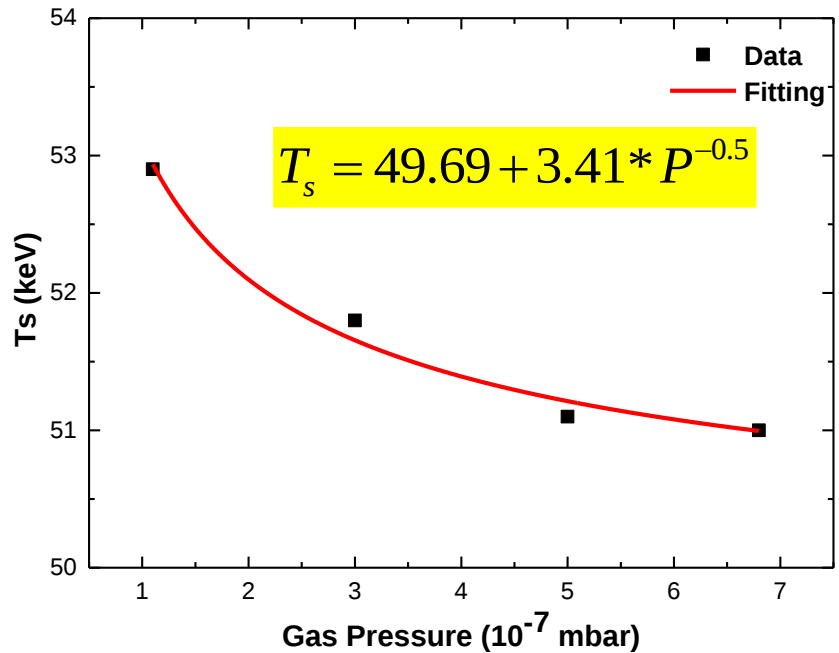
T_s VS RF Power



- T_s is at saturation even at 500W, which is consistent with the experimental study from VENUS (*Review of Scientific Instruments* 79, 033302 (2008)) and Mini-mafios (*Journal of Applied Physics* 76, 2662 (1994))
- T_s rapidly saturates with microwave power (above 500W, whatever the frequency)

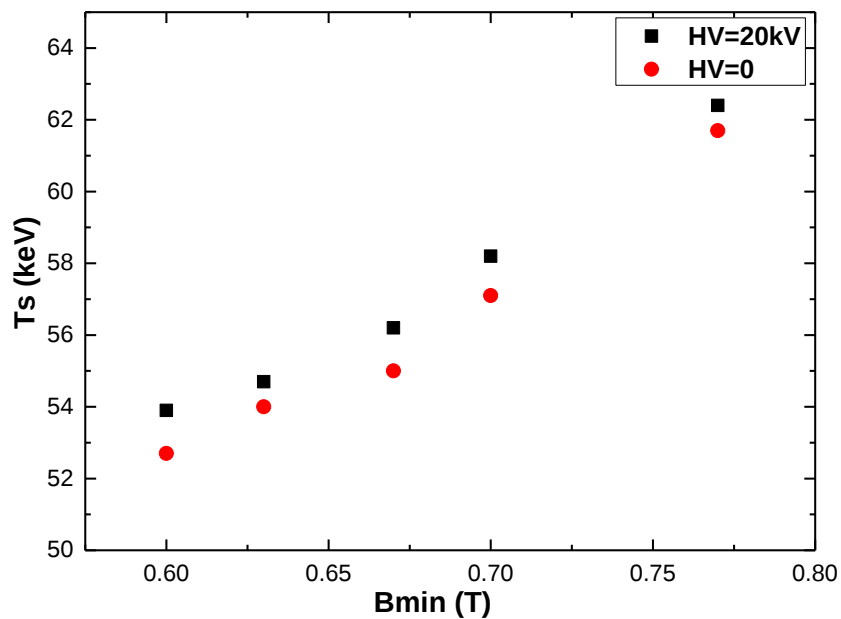
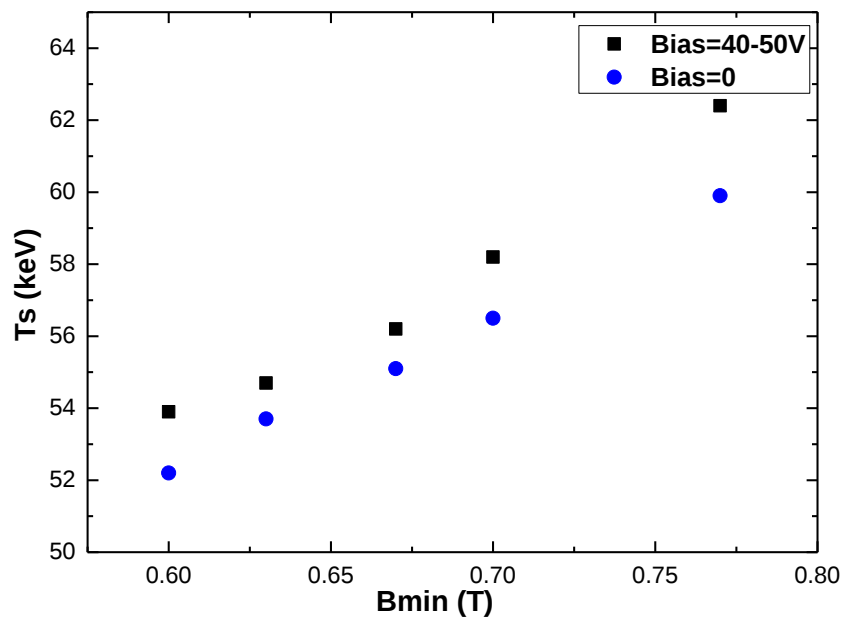
T_s VS Gas Pressure

Frequency (GHz)	Injection Pressure (10^{-7} mbar)	T_s (keV)
28	1	52.9
	2	51.8
	5	51.1
	7	51.0



➤ T_s is inversely proportional to the square root of the gas pressure
(Journal of Applied Physics 76, 2662 (1994))

Effect of Bias Voltage and HV

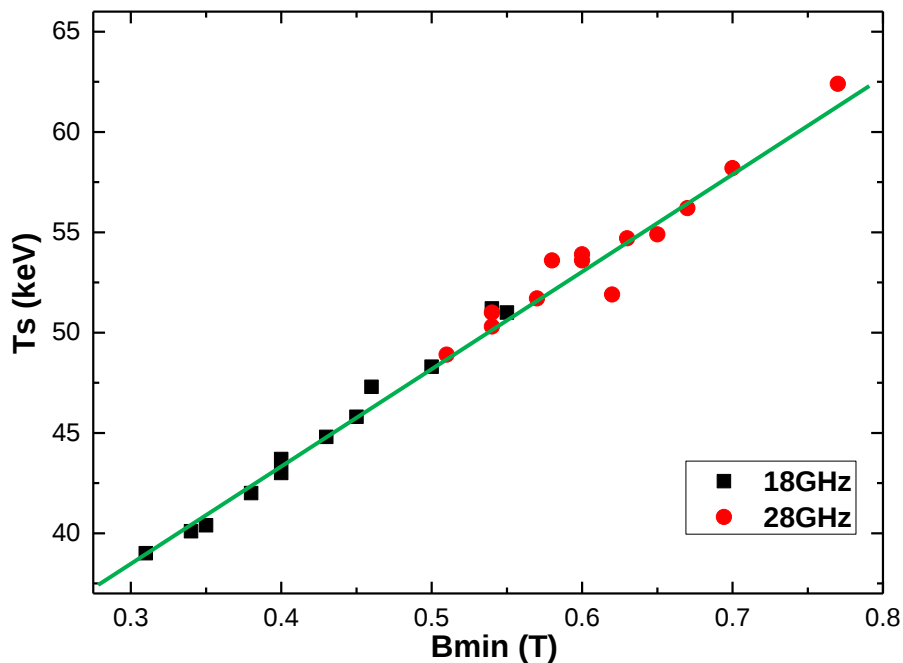


- T_s decreases with the decreasing of Bias and HV at each point
- T_s is slightly affected by biased disk and extraction voltage (difference less than 4%)

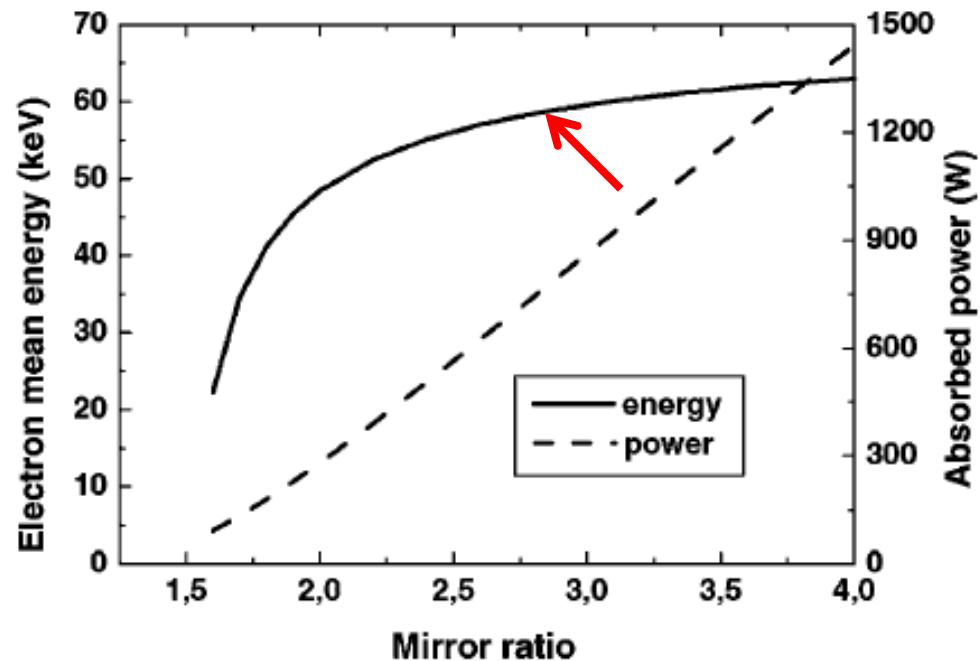


1st Conclusion

- ❑ T_s appears to be linearly dependent on $B_{\min}$
- ❑ T_s seems to be independent on ∇B_{ecr} and heating power
- ❑ T_s is inversely proportional to the square root of gas pressure
- ❑ T_s is slightly affected by biased disk and extraction voltage



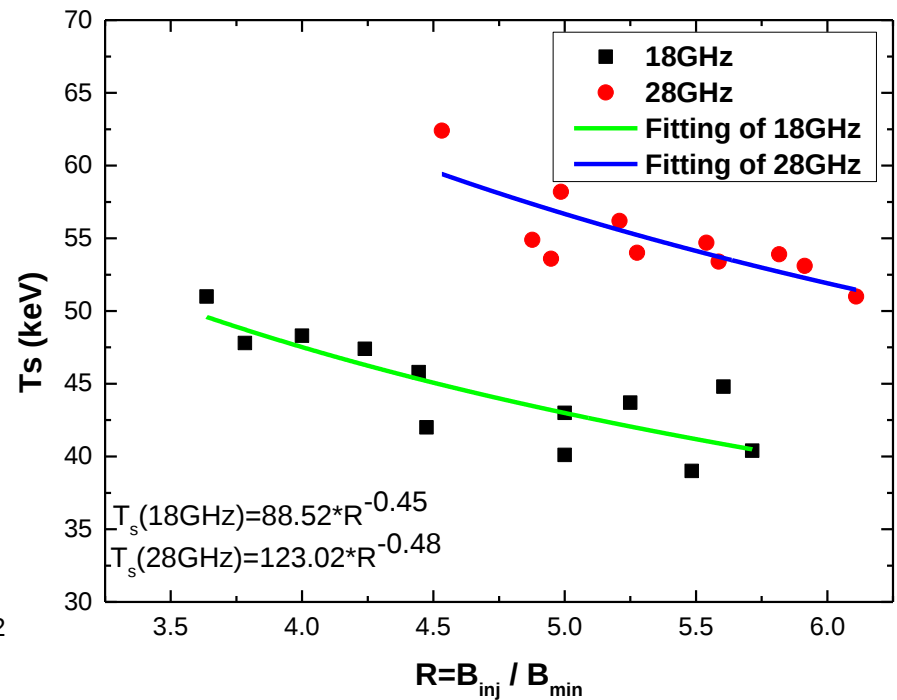
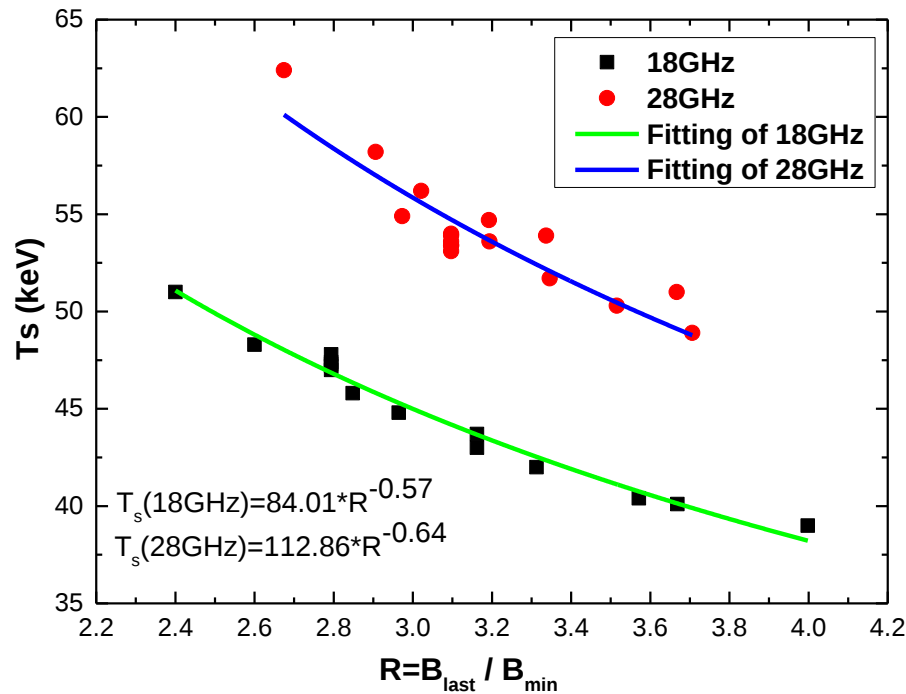
It is hard to understand why T_s appears to be dependent solely on the minimum magnetic field $B_{\min}$ since electrons move back and forth in a minimum-B structure



Electron energy saturates with mirror ratio

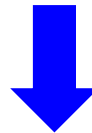
(Girard et al. *Journal of Computational Physics* 191 (2003))

T_s VS Mirror Ratio



T_s decreases with increasing mirror ratio $R = B_{\text{last}} / B_{\text{min}}$ or $B_{\text{inj}} / B_{\text{min}}$

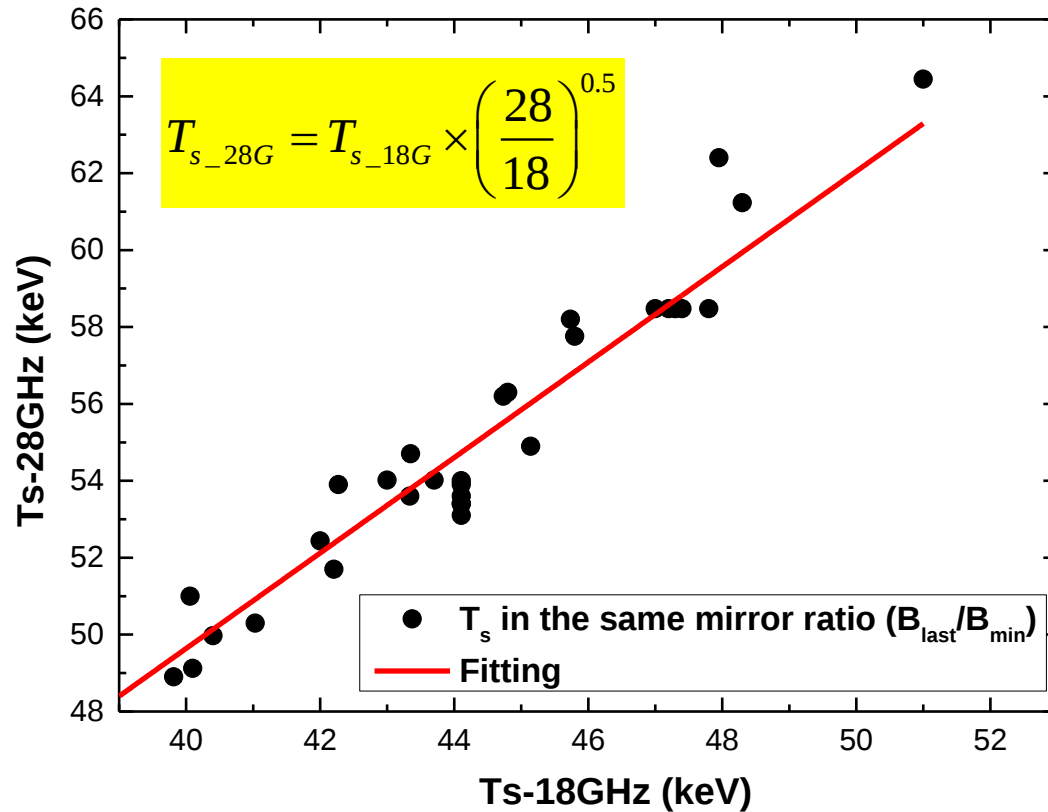
At high mirror ratios, electrons are more and more trapped in the min-B structure



They no longer cross the resonance after several travels back and forth

(Barue et al. Journal of Applied Physics 76, 2662 (1994))

Another Factor



T_s depends on the heating frequency f



2nd Conclusion

- ❑ All experiments were done at conventional mirror ratios where electrons are well trapped and high ion currents are extracted
- ❑ Next experiments will be done at lower mirror ratios



Acknowledgement

- Janilee Benitez, LBNL
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XXIII International Workshop on ECR Ion Source

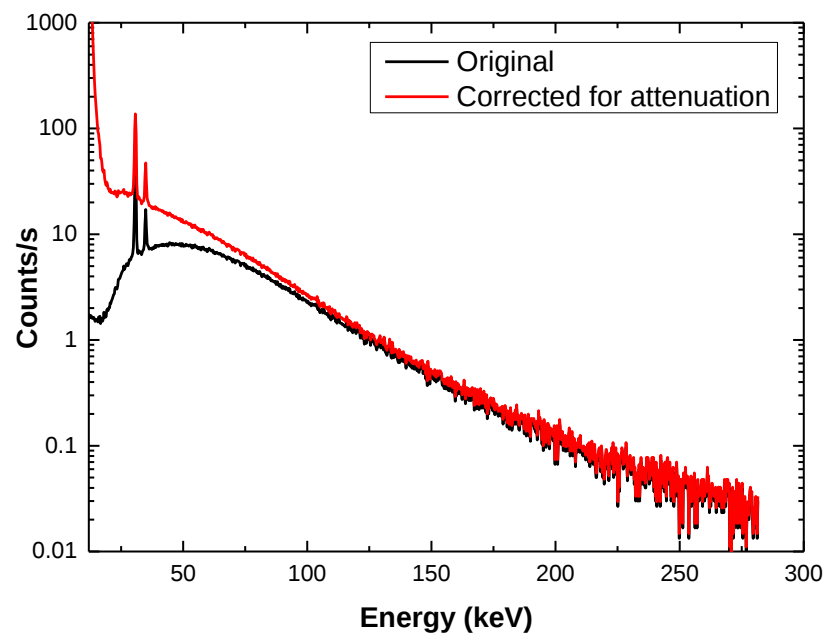
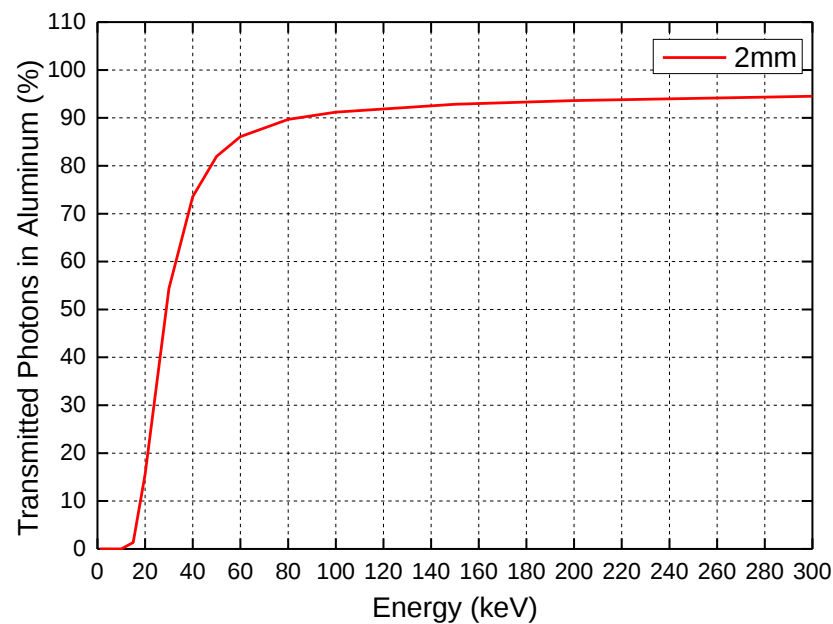
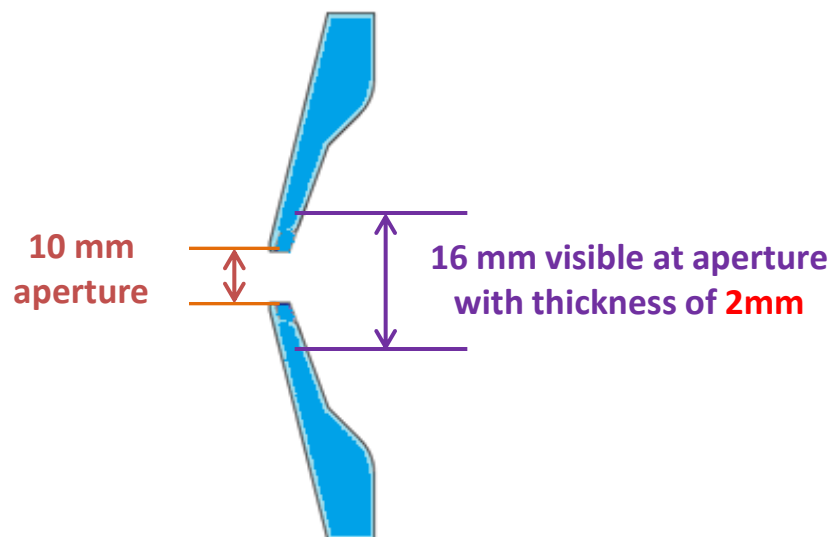


**Thanks for
your attention !**



September 10th – 14th, 2018

Appendix





Source Parameters

Beam	Xe27+
Frequency (GHz)	18、 28、 45
Power (w)	2000
Extraction Voltage (kV)	20
Biased Disk Voltage (-V)	~40-50
Injection Pressure (mbar)	$1\sim 2\times 10^{-7}$